

TECHNICAL DATA
Datasheet 4171, Rev. -**Three-Phase MOSFET BRIDGE, With Gate Driver and Optical Isolation****DESCRIPTION:** A 200 VOLT, 70 AMP, THREE PHASE MOSFET BRIDGE**ELECTRICAL CHARACTERISTICS PER MOSFET DEVICE**(T_j=25°C UNLESS OTHERWISE SPECIFIED)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
MOSFET SPECIFICATIONS					
Drain-to-Source Breakdown Voltage I _D = 500 μA, V _{GS} = 0V	BV _{DSS}	200	-	-	V
Continuous Drain Current T _C = 25 °C T _C = 90 °C	I _D	-	-	70 60	A
Pulsed Drain Current, Pulse Width limited by T _{jMax}	I _{DM}	-	-	300	A
Gate to Source Voltage	V _{GS}	-	-	+/-20	V
Gate- Source Leakage Current , V _{GE} = +/-20V	I _{GSS}	-	-	+/- 200	nA
Zero Gate Voltage Drain Current V _{DS} = 200 V, V _{GS} =0V T _i =25°C V _{DS} = 160 V, V _{GS} =0V T _i =125°C	I _{CSS}	-	-	1 3	mA mA
Static Drain-to-Source On Resistance, T _j = 25 °C T _j = 125 °C I _D = 50A, V _{GS} = 15V,	R _{DSon}	-	0.023 0.050	0.025 -	V
Maximum Thermal Resistance	R _{θJC}	-	-	0.35	°C/W
Maximum operating Junction Temperature	T _{jmax}	-40	-	150	°C
Maximum Storage Junction Temperature	T _{jmax}	-55	-	150	°C

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Over-Temperature Shutdown					
Over-Temperature Shutdown	T _{sd}	90	100	115	°C
Over-Temperature Output	T _{so}		10		10mV/°C
Over-Temperature Shutdown Hysteresis			20		°C

DIODES CHARACTERISTICS					
Continuous Source Current, T _C = 90 °C	I _S	-	-	60	A
Diode Forward Voltage, I _S = 50A, T _j = 25 °C	V _{SD}	-		1.5	V
Diode Reverse Recovery Time (I _S =50A, V _{DD} =100V, di/dt=100 A/μs)	t _{rr}	-	220	-	nsec
Gate Driver					
Supply Voltage	V _{CC}	10	15	20	V
Input On Current	H _{IN} , L _{IN}	2		5.0	mA
Opto-Isolator Logic High Input Threshold	I _{th}	-	1.6	-	mA
Input Reverse Breakdown Voltage	BV _{in}	5.0	-	-	V
Input Forward Voltage @ I _{in} = 5mA	V _F	-	1.5	1.7	V
Under Voltage Lockout	V _{CCUV}	11.5	-	12.5	V
ITRIP Reference Voltage ⁽¹⁾	I _{trip-ref}	2.5	2.6	2.7	V
Input-to-Output Turn On Delay	t _{ond}	-	TBD	-	nsec
Output Turn On Rise Time	t _r	-	TBD	-	
Input-to-Output Turn Off Delay	t _{offd}	-	TBD	-	
Output Turn Off Fall Time	t _f	-	TBD	-	
@ V _{CC} =100V, I _D =50A, T _C = 25					
Input-Output Isolation Voltage	-	1500	-	-	V

(1) ITRIP Cycle-by cycle current limit is internally set to 70A peak. The set point can be lowered by connecting a resistor between Itrip-ref and Gnd. The set point can be increased by connecting a resistor between Itrip-ref and +5V ref

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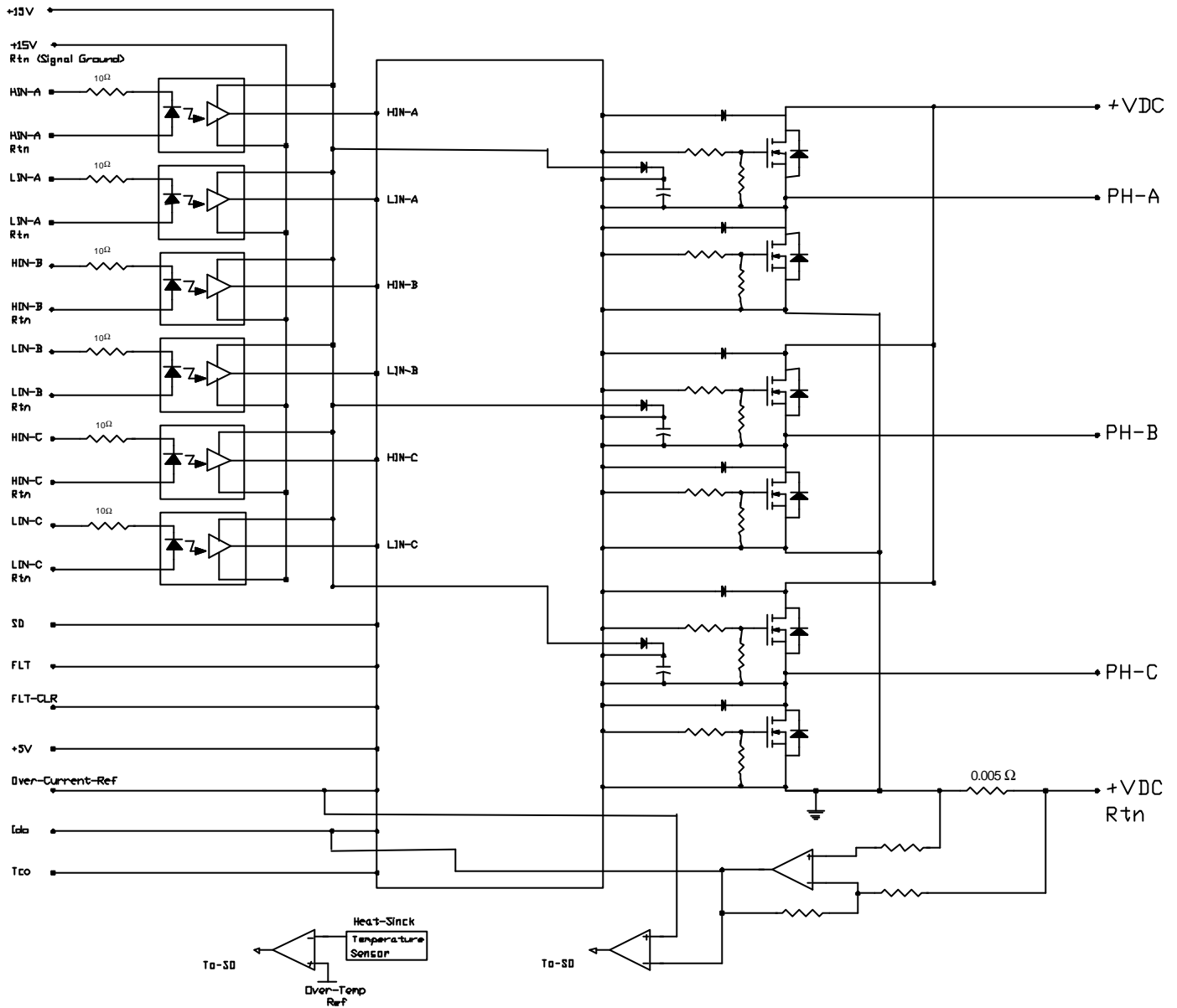
Pin Number	Function	Pin Number	Function
1	Isolated Input for High-side MOSFET of Phase A	18	NC
2	Return for Input at 1	19	+15V Input
3	NC	20	+15V Rtn (Signal Ground) ⁽³⁾
4	Isolated Input for Low-side MOSFET of Phase A	21	SD ⁽³⁾
5	Return for Input at 4	22	Fault Output ⁽³⁾
6	NC	23	Fault Clear Input ⁽³⁾
7	Isolated Input for High-side MOSFET of Phase B	24	+5V Output
8	Return for Input at 7	25	Over-Current Trip Set Point ⁽³⁾
9	NC	26	DC Bus Current Output with Total Gain of 0.06 V/A
10	Isolated Input for Low-side MOSFET of Phase B	27	Case Temperature Output with Gain of 0.010 V/°C
11	Return for Input at 10	28 & 29	Phase A Output
12	Isolated Input for High-side MOSFET of Phase C	30 & 31	Phase B Output
13	Return for Input at 12	32 & 33	Phase C Output
14	Isolated Input for Low-side MOSFET of Phase C	34 & 35	DC Bus "+VDC Return"
15	Return for Input at 14	36 & 37	DC Bus "+VDC" Input
16	NC	Case	Isolated From All Terminals
17	NC		

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Schematic Diagram:

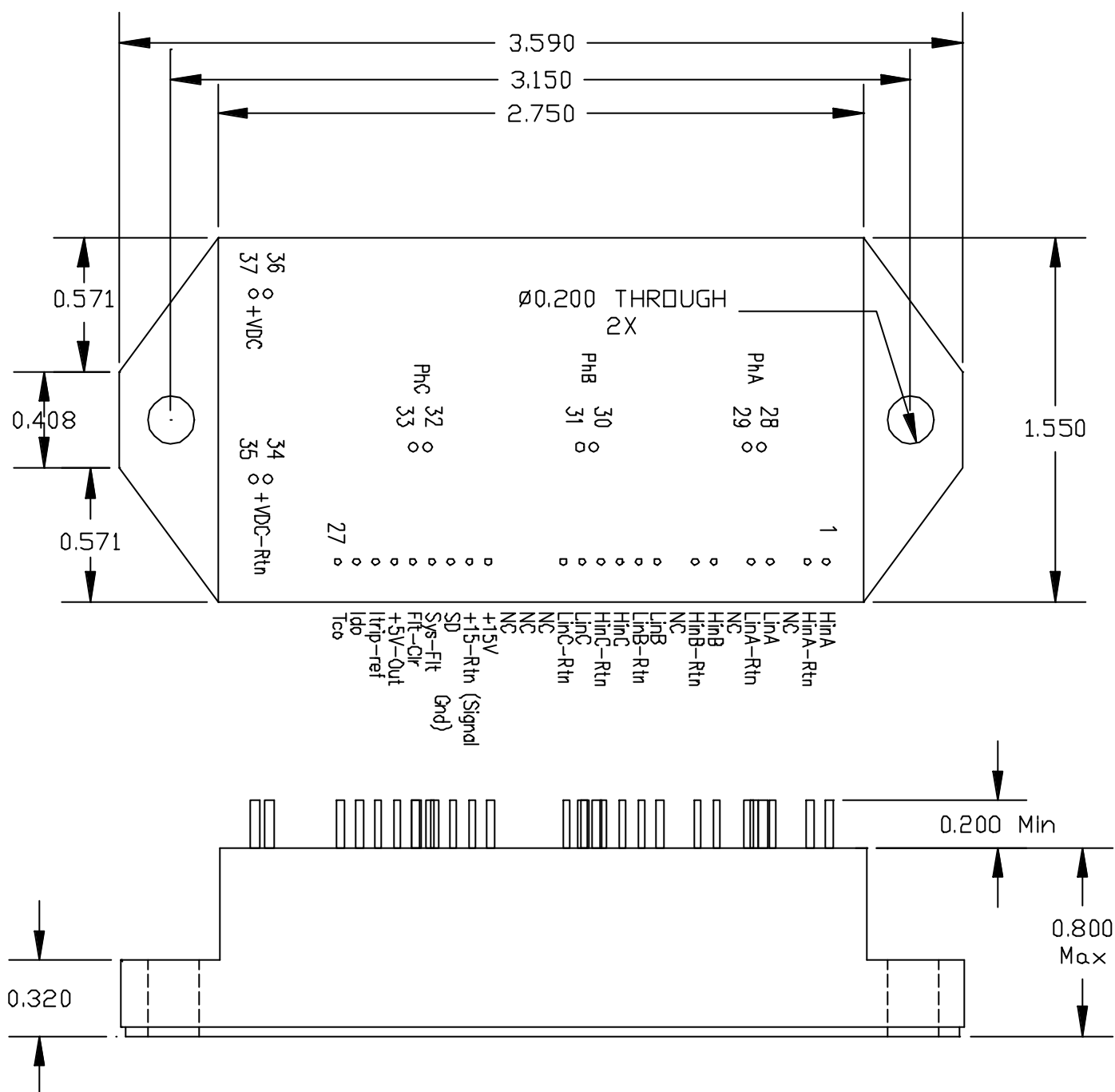


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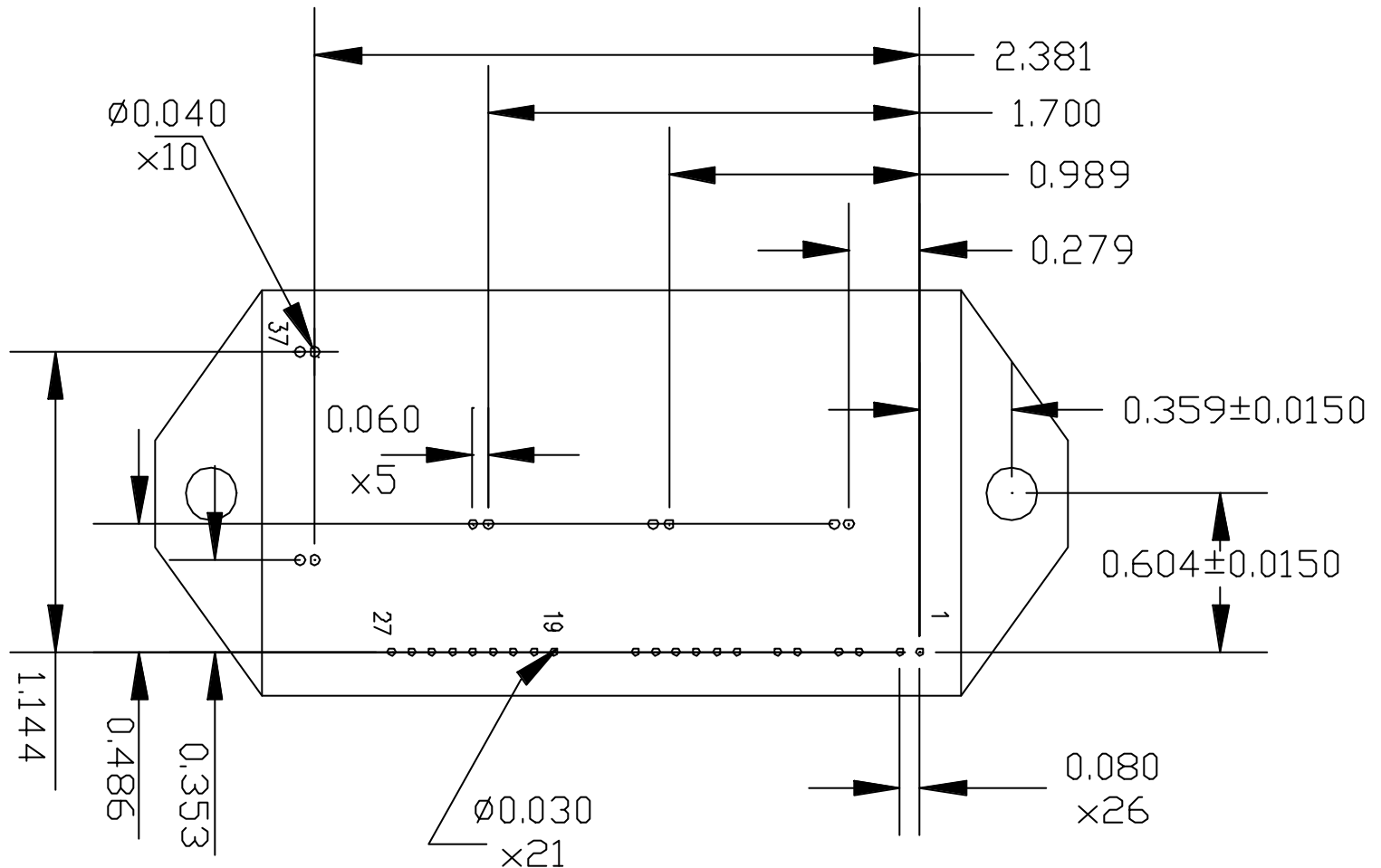
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Package Drawing Top View
(All dimensions are in inches, tolerance is +/- 0.010")



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Package Pin Locations**(All dimensions are in inches; tolerance is +/- 0.005" except otherwise specified)**

SENSITRON**TECHNICAL DATA****Datasheet 4171, Rev. -****Application Notes:****a- Shutdown Feature:**

- 1- Pin 21, SD is a dual function input/output, active low input. It is internally pulled high. As a low input, it shuts down all MOSFETs regardless of the Hin and Lin signals.
- 2- SD is also internally activated by the over-temperature shutdown, over-current limit, under-voltage shutdown, and desaturation protection.
- 3- Over-temperature shutdown, and over-current limit are not latching features.
- 4- Under-voltage shutdown is automatically reset once the VCC rises above the 12.1V threshold limit.
- 5- Desaturation shutdown is a latching feature and internally reset.
- 6- When any of the internal protection features are activated, SD is pulled down.
- 7- SD can be used to shutdown all MOSFETs by an external command. An open collector switch shall be used to pull down SD externally.
- 8- Also, SD can be used as a fault condition output. Low output at SD indicates a fault situation.

b- Fault Output Feature:

- 1- Pin 22, Flt is a dual function pin. It is internally pulled high. If pulled down, it will freeze the status of all the six MOSFETs regardless of the Hin and Lin signals
- 2- Pin 22 as an output reports desaturation protection activation. When desaturation protection is activated a low output for about 9 μ sec is reported.
- 3- If any other protection feature is activated, it will not be reported by Pin 22.

c- Fault Clear Output:

- 1- Pin 23, Flt-Clr is a fault clear input. It can be used to reset a latching fault condition, due to desaturation protection.
- 2- Pin 23 is internally pulled down. A latching fault due to desaturation can be cleared by pulling high this input.
- 3- An internal fault clear is activated after 100 μ sec delay. If desired to clear the fault earlier, this input can be used.

d- Signal Ground:

Pin 20, Signal Gnd is the signal ground for all signals at Pins 19 through 27. This ground is internally connected to the +VDC Rtn. **No external connection shall be established between Signal Gnd and +VDC Rtn.**

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